ne<mark>x</mark>peria

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Kind regards,

Team Nexperia



PBHV9115T150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistorRev. 02 - 9 January 2009Product data sheet

1. Product profile

1.1 General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8115T.

1.2 Features

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-150	V
I _C	collector current		-	-	-1	А
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -50 mA	100	220	-	



150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	base	—	
2	emitter		3
3	collector		
			sym013

3. Ordering information

Table 3. Order	ing information	on	
Type number	Package		
	Name	Description	Version
PBHV9115T	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4.	Marking codes	
Type num	iber	Marking code ^[1]
PBHV911	5T	W7*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

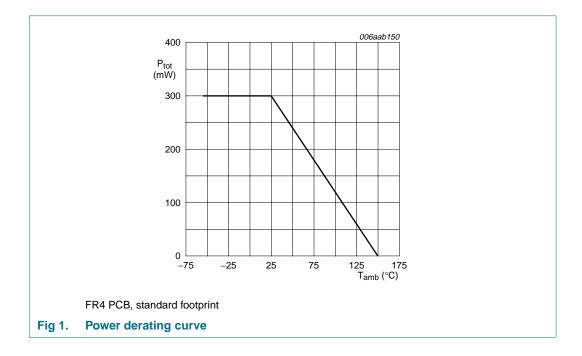
* = W: made in China

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

5. Limiting values

Table 5. In accorda	Limiting values nce with the Absolute Maximu	m Rating System (IE	C 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-200	V
V _{CEO}	collector-emitter voltage	open base	-	-150	V
V _{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-1	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	-2	A
I _{BM}	peak base current	single pulse; $t_p \leq 1 ms$	-	-400	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

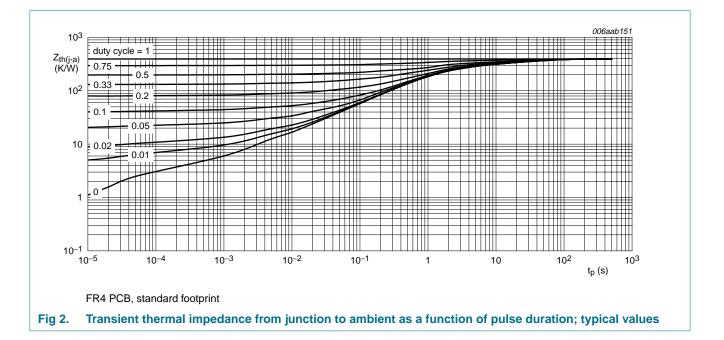


150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	417	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

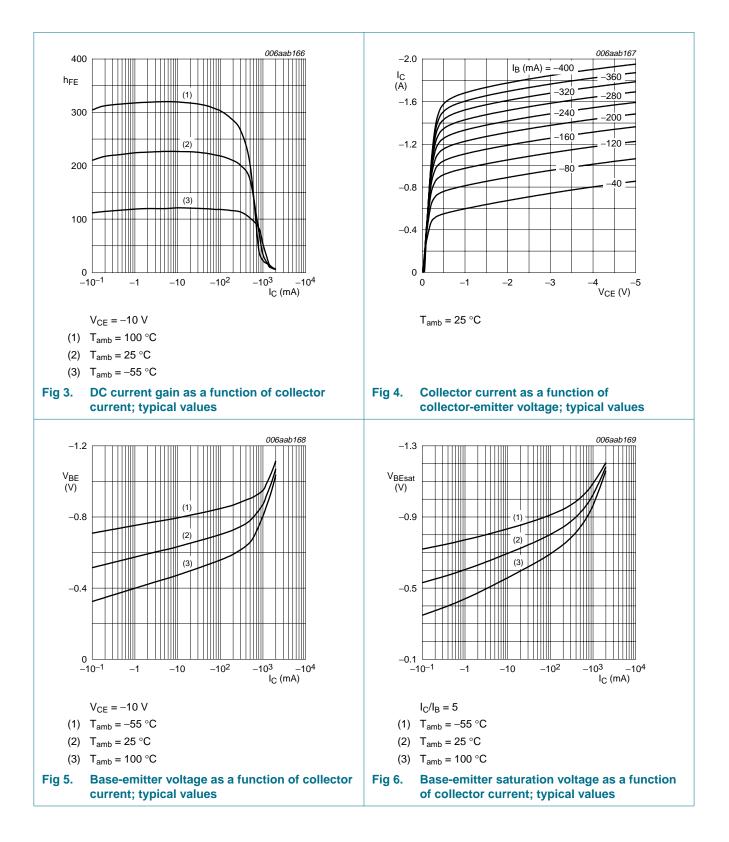
7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -120 V; I _E = 0 A		-	-	-100	nA
	current	$V_{CB} = -120 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-10	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -120 \text{ V}; \text{ V}_{BE} = 0 \text{ A}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -10 V$					
		I _C = -50 mA		100	220	-	
		$I_{\rm C} = -100 {\rm mA}$		100	220	-	
		$I_{\rm C} = -1$ A	<u>[1]</u>	10	30	-	
V _{CEsat} collector-emitter saturation voltage		$I_{C} = -100 \text{ mA}; I_{B} = -10 \text{ mA}$		-	-60	-120	mV
	saturation voltage	$I_{C} = -100 \text{ mA}; I_{B} = -20 \text{ mA}$		-	-50	-100	mV
		I _C = –500 mA; I _B = –100 mA		-	-150	-300	mV
V _{BEsat}	base-emitter saturation voltage	$I_{\rm C} = -1$ A; $I_{\rm B} = -200$ mA	<u>[1]</u>	-	-1.05	-1.2	V
f _T	transition frequency	$V_{CE} = -10 \text{ V}; I_E = -10 \text{ mA};$ f = 100 MHz		-	115	-	MHz
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -20 \ V; \ I_E = i_e = 0 \ A; \\ f = 1 \ MHz \end{array}$		-	10	-	pF
C _e	emitter capacitance	$\label{eq:Veb} \begin{array}{l} V_{EB}=-0.5 \text{ V}; \text{ I}_{C}=\text{i}_{c}=0 \text{ A};\\ \text{f}=1 \text{ MHz} \end{array}$		-	150	-	pF
t _d	delay time	$V_{CC} = -6 \text{ V}; \text{ I}_{C} = -0.5 \text{ A};$		-	8	-	ns
t _r	rise time	$I_{Bon} = -0.1 \text{ A}; I_{Boff} = 0.1 \text{ A}$		-	282	-	ns
t _{on}	turn-on time			-	290	-	ns
t _s	storage time			-	430	-	ns
t _f	fall time			-	300	-	ns
t _{off}	turn-off time			-	730	-	ns

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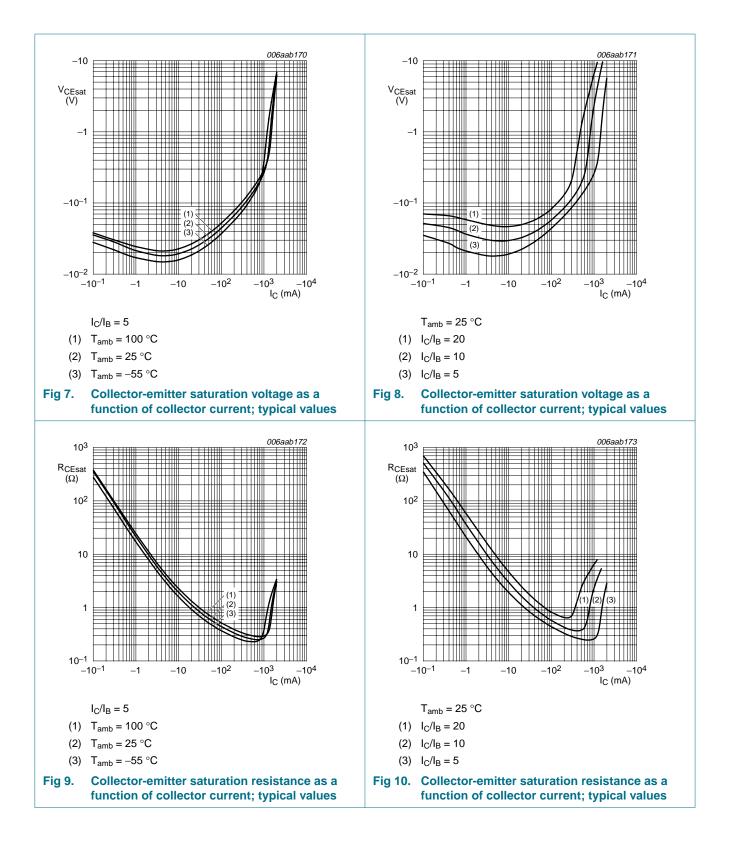
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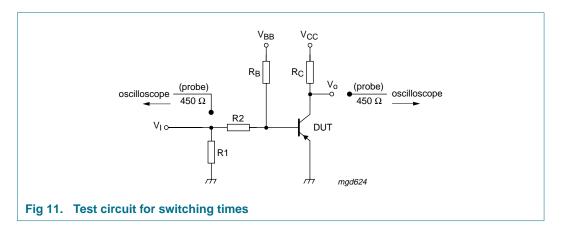
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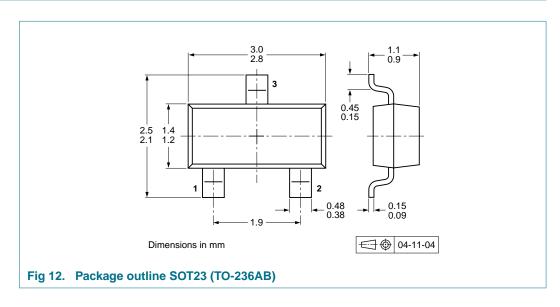
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

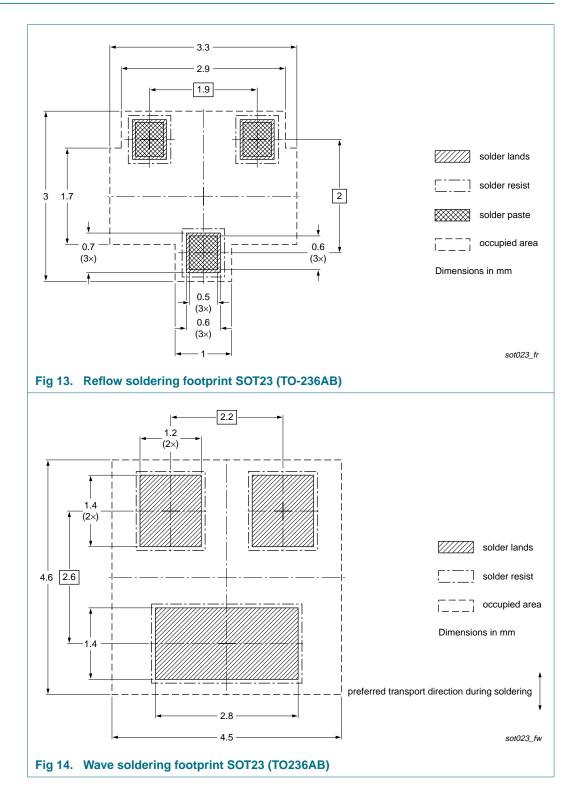
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			3000	10000
PBHV9115T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

11. Soldering



150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision I	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115T_2	20090109	Product data sheet	-	PBHV9115T_1
Modifications:	 <u>Table 5</u>: I_{BM} <u>Figure 4</u>: ar 	maximum value changed nended	from –100 mA to –400 m	nA
	 Section 13 	<u>'Legal information</u> ": update	d	
PBHV9115T_1	20080214	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

PBHV9115T

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

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